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# NTS4001N, NVS4001N

## MOSFET – Single, N-Channel, Small Signal, SC-70

30 V, 270 mA

### Features

- Low Gate Charge for Fast Switching
- Small Footprint – 30% Smaller than TSOP-6
- ESD Protected Gate
- AEC-Q101 Qualified and PPAP Capable – NVS4001N
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- Low Side Load Switch
- Li-Ion Battery Supplied Devices – Cell Phones, PDAs, DSC
- Buck Converters
- Level Shifts

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter		Symbol	Value	Units	
Drain-to-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-to-Source Voltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current (Note 1)	Steady State	T <sub>A</sub> = 25 °C	I <sub>D</sub>	270	mA
		T <sub>A</sub> = 85 °C		200	
Power Dissipation (Note 1)	Steady State	T <sub>A</sub> = 25 °C	P <sub>D</sub>	330	mW
Pulsed Drain Current		t = 10 μs	I <sub>DM</sub>	800	mA
Operating Junction and Storage Temperature		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150		°C
Source Current (Body Diode)		I <sub>S</sub>	270		mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T <sub>L</sub>	260		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).

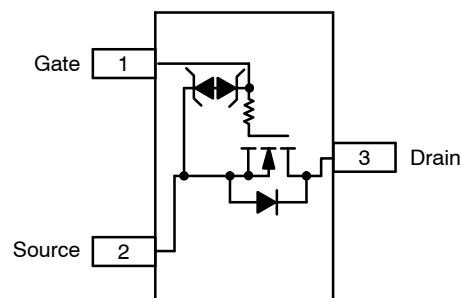


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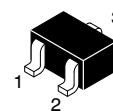
<http://onsemi.com>

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> Max
30 V	1.0 Ω @ 4.0 V	270 mA
	1.5 Ω @ 2.5 V	

### SC-70/SOT-323 (3 LEADS)

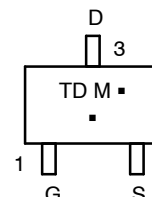


(Top View)



### MARKING DIAGRAM & PIN ASSIGNMENT

SC-70 / SOT-323  
CASE 419  
STYLE 8



TD = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
NTS4001NT1G	SC-70 (Pb-Free)	3000 / Tape & Reel
NVS4001NT1G	SC-70 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTS4001N, NVS4001N

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			60		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}$			1.0	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			$\pm 1.0$	$\mu\text{A}$

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 100\ \mu\text{A}$	0.8	1.2	1.5	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-3.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.0\text{ V}, I_D = 10\text{ mA}$		1.0	1.5	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 10\text{ mA}$		1.5	2.0	
Forward Transconductance	$g_{FS}$	$V_{DS} = 3.0\text{ V}, I_D = 10\text{ mA}$		80		mS

### CHARGES AND CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 5.0\text{ V}$		20	33	pF
Output Capacitance	$C_{OSS}$			19	32	
Reverse Transfer Capacitance	$C_{RSS}$			7.25	12	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 5.0\text{ V}, V_{DS} = 24\text{ V}, I_D = 0.1\text{ A}$		0.9	1.3	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.2		
Gate-to-Source Charge	$Q_{GS}$			0.3		
Gate-to-Drain Charge	$Q_{GD}$			0.2		

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 5.0\text{ V}, I_D = 10\text{ mA}, R_G = 50\ \Omega$		17		ns
Rise Time	$t_r$			23		
Turn-Off Delay Time	$t_{d(OFF)}$			94		
Fall Time	$t_f$			82		

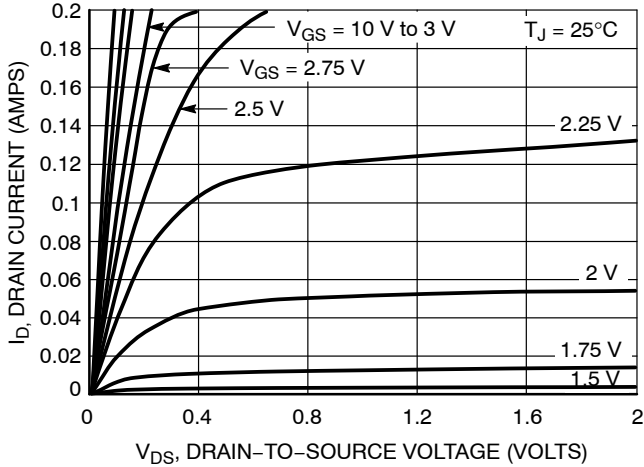
### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 10\text{ mA}$	$T_J = 25^\circ\text{C}$	0.65	0.7	V
			$T_J = 125^\circ\text{C}$	0.43		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 8.0\text{ A}/\mu\text{s}, I_S = 10\text{ mA}$		5.0		ns

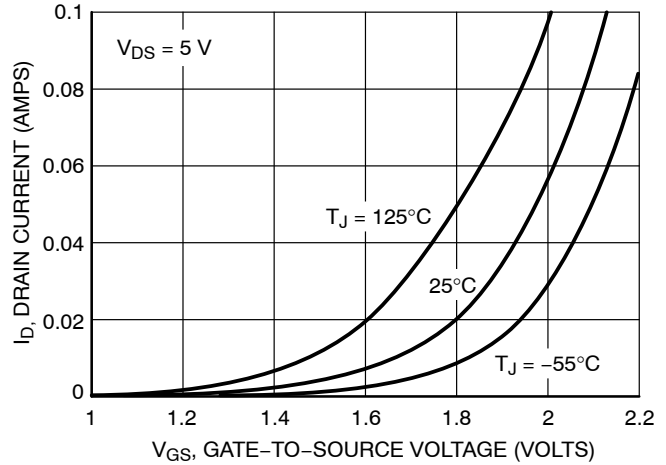
2. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
3. Switching characteristics are independent of operating junction temperatures.

# NTS4001N, NVS4001N

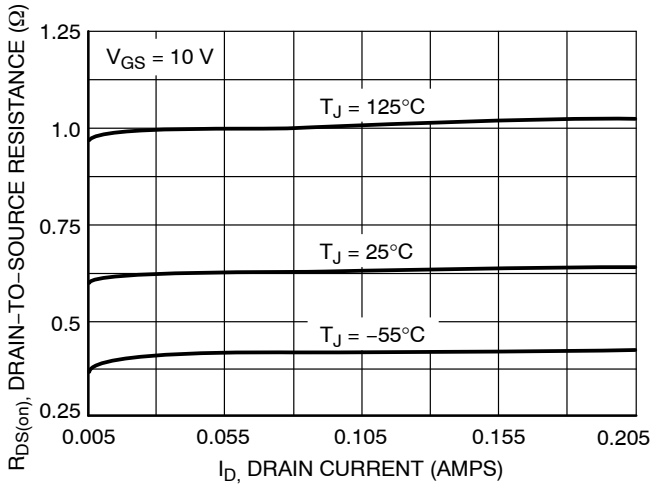
## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



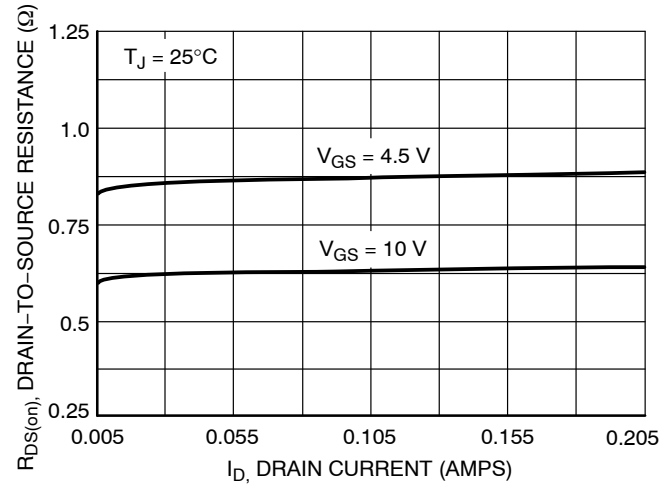
**Figure 1. On-Region Characteristics**



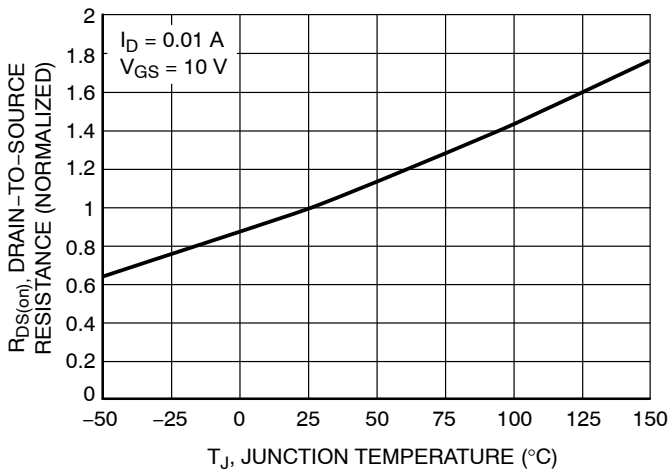
**Figure 2. Transfer Characteristics**



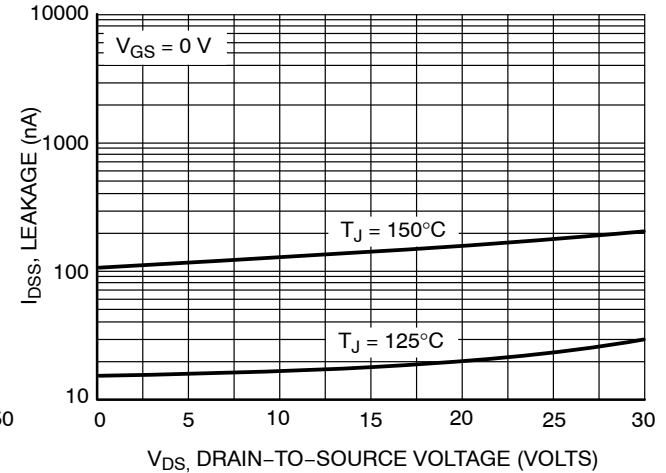
**Figure 3. On-Resistance vs. Drain Current and Temperature**



**Figure 4. On-Resistance vs. Drain Current and Gate Voltage**



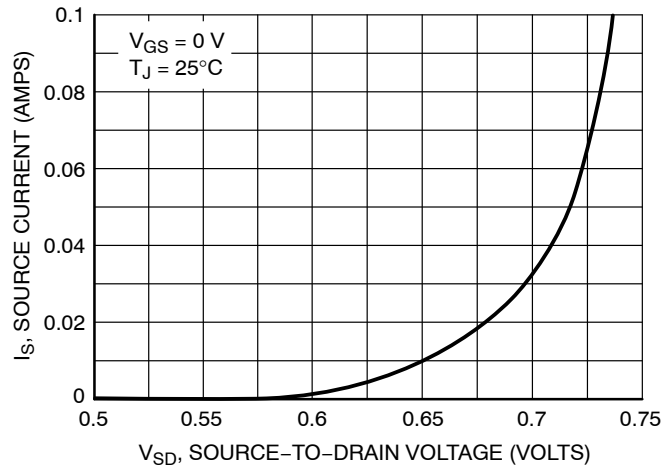
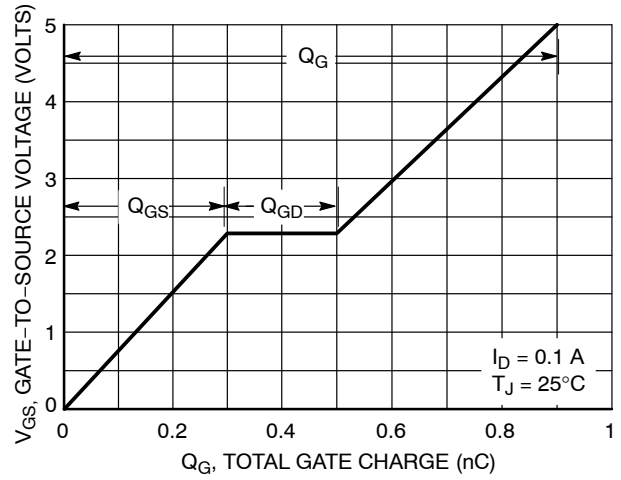
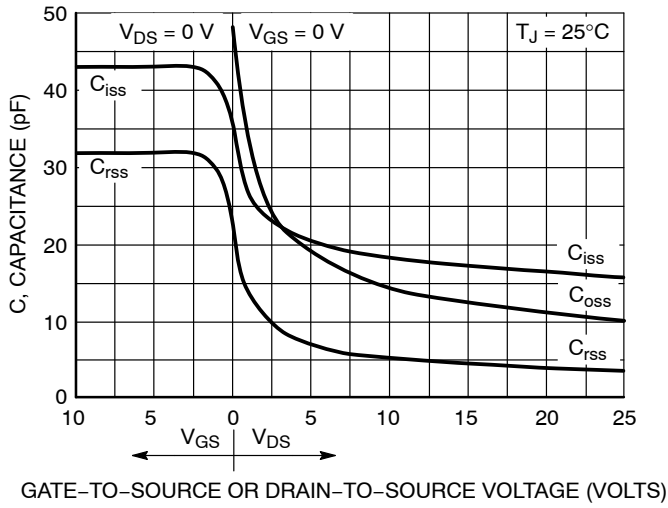
**Figure 5. On-Resistance Variation with Temperature**



**Figure 6. Drain-to-Source Leakage Current vs. Voltage**

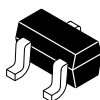
# NTS4001N, NVS4001N

## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

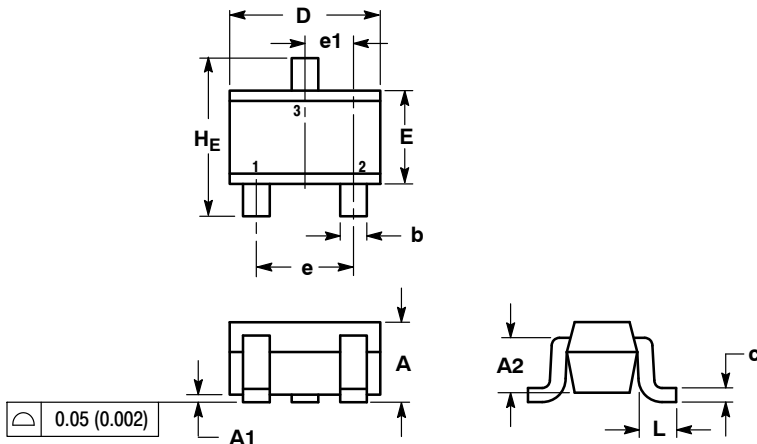
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SCALE 4:1

SC-70 (SOT-323)  
CASE 419-04  
ISSUE N

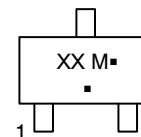
DATE 11 NOV 2008



NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

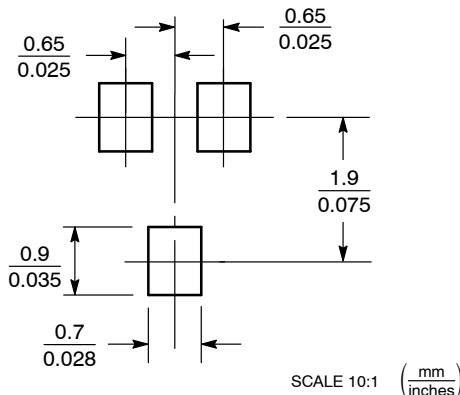
### GENERIC MARKING DIAGRAM



XX = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

### SOLDERING FOOTPRINT\*




\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 6: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE
				STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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